Thursday - March 8th, 2018	
8:50 - 9:00	**Marek Godlewski** - Conference opening address
9:00 - 10:40	**Harm Knoops** - Atomic Layer Deposition for Perovskite Solar Cells - Th1
	Rafał Pietruszka - Innovative solar cell structures based on oxides films - Th2
	David Tröger - TiOx based Passivation as full area Contacts for Si Solar Cells - Th3
	Małgorzata Kot - Application of ALD-Al2O3 in Perovskite Solar Cells - Th4
	Konrad Wojciechowski - Atomic layer deposition in perovskite solar cells - Th5
10:40 - 11:20	Coffee Break
11:20 - 13:00	**Maciej Sawicki** - Metal-Oxide-Semiconductor Structures of Ferromagnetic Semiconductors - Th6
	Maxim Kozodaev - Improved ferroelectric performance of La:Hf0.5Zr0.5O2 thin films - Th7
	Franciszek Krok - Formation of crystalline conductive titanium oxide (TiO) nanowires on reduced SrTiO3(100) - Th8
	Martin Knaut - Atomic layer deposition and 3D nanoscale substrates - nanowires - nanotubes and nanopores - Th9
	Christoph Hossbach - Properties of some rare-earth oxide films grown by Atomic Layer Deposition - Th10
13:00 - 14:20	Lunch
14:20 - 16:20	**Anna Słońska-Zielonka** - Novel oxide materials with antibacterial properties deposited by low-temperature ALD - Th11
	Michal M. Godlewski - Oxide nanoparticles as a novel carrier of drugs through the blood-brain barrier - Th12
	Izabela Serafińska - High-k Oxide Nanolayers – the Future of Medicine - Th13
	Violetta Sessi - Integration of dielectric and ferroelectric ALD layers in silicon nanowire-based devices - Th14
	Sebastian Killge - High-aspect-ratio TSVs with thALD/PEALD tantalum-based barrier layer, thALD Ruthenium seed layer and subsequent copper electroplating - Th15
	Canceled - **Jonas Gessler** - Comparison of High-K Dielectrics by Thermal and Plasma ALD - Th16
16:20 - 17:00	Coffee Break
17:00 - 18:00	**POSTER SESSION** **P1** - Magdalena Szindler, TiO2 thin films deposited by ALD method for silicon solar cells **P2** - Marek Szindler, Al2O3 thin film deposited by ALD method for photovoltaic application **P3** - Karsten Henkel, Electrical and spectroscopic investigation on AlN films prepared by PEALD using different plasma sources **P4** - Yong Bin Lee , Influence of Charge Injection through Interfacial Layer for the Ferroelectric Field Effect Transistor using Hf0.5Zr0.5O2 Thin Films **P5** - Young Hwan Lee, Effective phase transformation kinetics of ferroelectric Hf0.5Zr0.5O2 films by the presence of the top electrode **P6** - Hyeonwoo Park, Comparative study on models of the voltage drop phenomena in ferroelectric thin films **P7** - Jarosław Kaszewski, Oxide nanoparticles for antibacterial printing varnishes **P8** - Paulina Boryło, Characteristics of zinc oxide thin films deposited according to ALD method **P9** - Piotr Caban, Application Of The ALD Method In ZnO/GaAs Solar Cells Fabrication **P10** - Marcin Kieliszczyk, Technology and properties of MIS structures with ALD dielectric layers with applications for NVSM non-volatile memory **P11** - Monika Ożga, Application of the ALD for the Nucleation of ZnO Nanorods Growth by Hydrothermal Method **P12** - Katarzyna Gas, ZnTe Nanowires Overgrown by Atomic Layer Deposited (Zn,Co) Oxides: Raman Scattering Studies
19:00 - ???	**Conference Banquet**

Friday - March 9th, 2018	
9:00 - 10:40	**Christian Wenger** - Optimized Switching Performance of HfO2-based Resistive Memory Arrays - Fr1
	Ulrich Böttger - Ultra-fast resistive switching in tantalum oxide thin films - Fr2
	Melanie Herzig - Investigation And Optimization Of NbOx-based Threshold Switching Devices For Neuromorphic Computing - Fr3
	Luca Di Piazza - Comparison Of Ferroelectric Doped Al:HfO2 And Si:HfO2 Capacitors With Silicon As Electrodes For Memory Applications - Fr4
	Igor Stolichnov - Robust ferroelectricity - coexistence of phases and weak size effects in Hf1-xZrxO2 (HZO) capacitors: an insight from PFM - Fr5
10:40 - 11:20	Coffee Break
11:20 - 13:00	**Sven Jachalke** - Pyroelectricity of silicon-doped hafnium oxide thin films - Fr6
	Clemens Mart - Wake-up effect of pyroelectric response in doped HfO2 - Fr7
	Sven Kirbach - Piezoelectricity In Si-doped HfO2 Thin Films - Fr8
	Andris Anspoks - Local structural investigation of Hafnia-Zirconia Polymorphs by extended x-ray absorption spectroscopy (EXAFS) - Fr9
	Andrei Zenkevich - Potential Distribution Across Ferroelectric-HfO2 Based Memory Capacitors Measured by Operando HAXPES - Fr10
13:00 - 14:20	Lunch
14:20 - 16:00	**Dieter Schmeißer** - Ionicity and inhomogeneous charge distribution by polarons and excitons in Hafnia - Fr11
	Max Falkowski - Impact Of Small Scale Doping Inhomogeneity In HfO2 On Phase Stability: An Ab Initio Study - Fr12
	Alfred Kersch - A Model Of Crystallization Kinetics In Hafnia-Zirconia Based On Ab Initio Data - Fr13
	Fenja Berg - Processing of sputtered ferroelectric hafnium oxide - Fr14
	Terence Mittmann - Comparison of ferroelectric properties in ALD vs. PVD deposited Hf1-xZrxO2 films - Fr15
16:00 - 16:40	Coffee Break
16:40 - 17:40	**Monica Materano** - Built-in bias generation in ZrO2-based AFE-Capacitors - Fr16
	Min Hyuk Park - Structural origin of temperature dependent ferroelectricity in fluorite structured ferroelectrics for various energy - related applications - Fr17
	Tony Schenk - Stress and Texture in HfO2-based Ferroelectric Thin Films - Fr18
17:40 - 17:50	**Marek Godlewski** - Conference closing address
18:00 - 19:00	Dinner